

**10/694,500****Patent  
IBM Docket No. FIS920020001US2**In the claims:

Claims 1 - 8 (Canceled).

9. (Currently amended) An edge seal around the periphery of an integrated circuit device comprising:

a semiconductor substrate;

a layer of low-k dielectric material over the semiconductor substrate;

a layer of hard material over or under the layer of low-k dielectric material, the layer of hard material selected from the group consisting of a dielectric material and a hard mask material; and

an edge seal structure around the periphery of an integrated circuit device comprising:

a metallic wall of a high conductivity metal in the layer of low-k dielectric material and in the layer of hard material; and

a layer of insulation material on sidewalls of the metallic wall between the metallic wall and the low-k dielectric material and between the metallic wall and the layer of hard material, wherein the insulation material and low-k dielectric material are different materials and wherein the insulation material is selected from the group consisting of SiO<sub>2</sub>, SiC, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, diamond like carbon, polyimide and combinations thereof.

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10. (Original) The edge seal of claim 9 wherein the low-k dielectric material comprises SiLK or fluoridized polyimide.
11. (Previously presented) The edge seal of claim 9 wherein the layer of hard material comprises a bottom layer on the semiconductor substrate under the low-k dielectric material and a top moisture barrier on the low-k dielectric material.
- Claim 12. (Canceled)
13. (Original) The edge seal of claim 9 further comprising a barrier layer between the metallic wall and the insulation material wherein the barrier layer is selected from the group consisting of tantalum, tantalum nitride, chromium/ chromium oxide, titanium, titanium nitride, tungsten silicide and combinations thereof.
14. (Original) The edge seal of claim 9 wherein the high conductivity metal is copper.
15. (Original) The edge seal of claim 9 wherein the thickness of the insulation material is 0.05 microns to 0.5 microns.

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16. (Currently amended) An edge seal around the periphery of an integrated circuit device comprising:

a semiconductor substrate;

a layer of dielectric material over the semiconductor substrate, the layer of dielectric material comprising a low-k dielectric material; and

an edge seal structure around the periphery of an integrated circuit device comprising:

a metallic wall of a high conductivity metal in the layer of dielectric material, wherein the metallic wall comprises spaced-apart via-studs physically connected by an interconnection line;

and

a layer of insulation material between the metallic wall and the dielectric material, wherein the insulation material and dielectric material are different materials, ~~wherein there are two spaced-apart metallic walls physically connected by a metallic cross piece in the at least one layer of dielectric material, each of the metallic walls comprising two spaced-apart sides, and there is a~~ and wherein the layer of insulation material is between the dielectric material and each of the via-studs ~~metallic walls with each layer of insulation material being of a different material than the dielectric material.~~

Claim 17 (Canceled).

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18. (Currently amended) An edge seal around the periphery of an integrated circuit device comprising:

a semiconductor substrate;

a layer of dielectric material over the semiconductor substrate, the layer of dielectric material comprising a low-k dielectric material; and

an edge seal structure around the periphery of an integrated circuit device comprising:

a metallic wall comprising two spaced-apart via studs physically connected by an interconnection line sides in the layer of dielectric material; and

a wall of insulation material ~~only~~ between the metallic wall and the periphery of the integrated circuit device, wherein the insulation material and dielectric material are different materials.